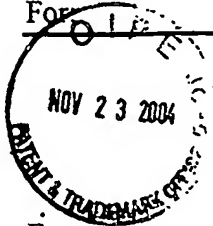


Applicant: Yongjun Hu
 Serial No.: 10/771,828
 Filing Date: February 4, 2004
 For: PROCESS FOR FORMING A DIFFUSION BARRIER MATERIAL NITRIDE FILM

Confirmation No.: 3960
 Att'y Docket No.: 11675.73.1.2.1
 Group: 2818



INFORMATION DISCLOSURE CITATIONS MADE BY APPLICANT

U.S. Patent Documents

Examiner Initial*	Document Number	Issue Date	Name
<u>aw</u> 1	4,782,380	11/01/88	Shankar et al.
<u>cy</u> 2	4,847,111	07/11/89	Chow et al.
<u>cy</u> 3	4,897,368	01/30/90	Kobushi et al.
<u>ms</u> 4	4,927,505	05/22/90	Sharma et al.
<u>ms</u> 5	4,976,839	12/11/90	Inoue
<u>ms</u> 6	5,075,251	12/24/91	Torres et al.
<u>ms</u> 7	5,162,262	11/10/92	Ajika et al.
<u>ms</u> 8	5,188,979	02/23/93	Filipiak
<u>ms</u> 9	5,286,676	02/15/94	Kruger et al.
<u>ms</u> 10	5,318,924	06/07/94	Lin et al.
<u>ms</u> 11	5,631,479	05/97	Shiga
<u>ms</u> 12	5,633,200	05/27/97	Hu
<u>ms</u> 13	5,665,209	09/09/97	Byun
<u>ms</u> 14	5,688,718	11/18/97	Shue
<u>ms</u> 15	6,080,657	06/27/00	Liu et al.
<u>ms</u> 16	6,472,264 B1	10/29/02	Agarwal
<u>ms</u> 17	6,489,194 B1	12/03/02	Agarwal

Examiner:

Quar Hoang

Date Considered:

01/2005

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Foreign Patent Documents

Examiner Initial*	Document Number	Publication Date	Country or Patent Office	Translation
<u>h</u> 18	3-11735 (A)	01/21/91	Japan	no
<u>h</u> 19	5-347274 (A)	12/27/93	Japan	no

Other Documents

(including author, title, pertinent pages, etc.)

Examiner Initial*

- h 20 Lin J. et al., *Aluminum Contact Filling and Planarization With Pulsed Laser*, Materials Research Society, Conference Proceedings ULSI-VII, pp. 535-540, 1992.
- h 21 Shingubara S. et al, *Submicron Hole Filling Characteristics Employing ECR Al Sputtering with High Magnetic Field*, Materials Research Society, Conference Proceedings ULSI-VIII, p. 257-266, 1993.
- h 22 Joshi R.V. et al., *Collimated Sputtering for Refractory Metal Liners for Sub-Half Micron Technology*, Materials Research Society, Conference Proceedings ULSI-VIII, pp. 273-279, 1993.
- h 23 Hsieh J. J. et al., *Collimated Liners: Process Modeling and Material Characteristics*, Materials Research Society, Conference Proceedings ULSI-IX, pp. 207-213, 1994.
- h 24 Ramaswami S. et al., *Development of a Coherent Ti/TiN Process for Sub-Half Micron Technologies*, Materials Research Society, Conference Proceedings ULSI-IX, pp. 215-221, 1994.

References Cited by Applicants

While the filing of Information Disclosure Statements is voluntary, the procedure is governed by the guidelines of Section 609 of the Manual of Patent Examining Procedure and 37 C.F.R. §§ 1.97 and 1.98. To be considered a proper Information Disclosure Statement, Form PTO-1449 shall be accompanied by a copy of each listed patent or publication or other item of information and a translation of the pertinent portions of foreign documents (if an existing translation is readily available to the applicant), an explanation of relevance of each reference not in the English language, and should be submitted in a timely manner as set out in MPEP Sec. 609.

Examiner:

Date Considered:

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07/2005

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Examiners will consider all citations submitted in conformance with 37 C.F.R. § 1.98 and MPEP Sec. 609 and place their initials adjacent the citations in the spaces provided on this form. Examiners will also initial citations not in conformance with the guidelines which may have been considered. A reference may be considered by the Examiner for any reason whether or not the citation is in full conformance with the guidelines. A line will be drawn through a citation if it is not in conformance with the guidelines AND has not been considered. A copy of the submitted form, as reviewed by the Examiner, will be returned to the applicant with the next communication. The original of the form will be entered into the application file.

Each citation initialed by the Examiner will be printed on the issued patent in the same manner as references cited by the Examiner on Form PTO-892.

The reference designations "A1," "A2," etc. (referring to Applicant's reference 1, Applicant's reference 2, etc.) will be used by the Examiner in the same manner as Examiner's reference designations "A," "B," "C," etc. on Office Action Form PTO-1142.

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Examiner: Qing Huang Date Considered: 5/2005

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